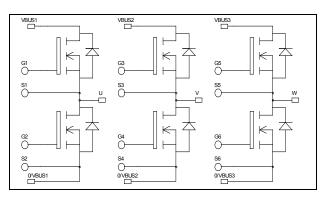
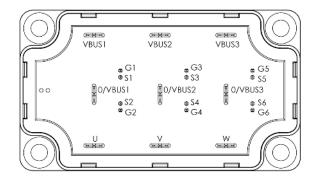


Triple phase leg MOSFET Power Module





## Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>DSS</sub>	Drain - Source Breakdown Voltage		1000	V
I <sub>D</sub>	Continuous Drain Current	$T_c = 25^{\circ}C$	22	
		$T_c = 80^{\circ}C$	17	А
I <sub>DM</sub>	Pulsed Drain current	88		
V <sub>GS</sub>	Gate - Source Voltage		±30	V
R <sub>DSon</sub>	Drain - Source ON Resistance		420	mΩ
P <sub>D</sub>	Maximum Power Dissipation $T_c = 25^{\circ}C$		390	W
I <sub>AR</sub>	Avalanche current (repetitive and non repetitive)		25	А
E <sub>AR</sub>	Repetitive Avalanche Energy		50	im I
E <sub>AS</sub>	Single Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

## $V_{DSS} = 1000V$ $R_{DSon} = 350m\Omega \text{ typ} @ \text{Tj} = 25^{\circ}\text{C}$ $I_D = 22A @ \text{Tc} = 25^{\circ}\text{C}$

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

#### • Power MOS 7<sup>®</sup> FREDFETs

- Low R<sub>DSon</sub>
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
  - High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
  - Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS Compliant

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## All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$	$T_j = 25^{\circ}C$			100	μA
		$V_{GS} = 0V, V_{DS} = 800V$	$T_j = 125^{\circ}C$			500	
R <sub>DS(on)</sub>	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 11A$			350	420	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$		3		5	V
I <sub>GSS</sub>	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$				±100	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	Input Capacitance	$V_{GS} = 0V$		5.2		
Coss	Output Capacitance	$V_{\rm DS} = 25 V$		0.88		nF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1 MHz		0.16		
$Q_{g}$	Total gate Charge	$V_{GS} = 10V$		186		
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 500V$		24		nC
$Q_{gd}$	Gate – Drain Charge	$I_D = 22A$		122		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive switching @ 125°C		18		ns
T <sub>r</sub>	Rise Time	$V_{GS} = 15V$		12		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 670V$ $I_D = 22A$ $R_G = 5\Omega$		155		
$T_{\rm f}$	Fall Time			40		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 22A, R_G = 5\Omega$		900		
E <sub>off</sub>	Turn-off Switching Energy			623		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 22A, R_G = 5\Omega$		1423		Ŧ
E <sub>off</sub>	Turn-off Switching Energy			779		μJ

### Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$			22	•
	(Body diode)		$Tc = 80^{\circ}C$			17	А
V <sub>SD</sub>	Diode Forward Voltage	$V_{GS} = 0V, I_S = -22A$				1.3	V
dv/dt	Peak Diode Recovery <b>1</b>					18	V/ns
t <sub>rr</sub>	Payara Pasayary Tima		$T_j = 25^{\circ}C$			320	
	Reverse Recovery Time	$I_{S} = -22A$ $V_{R} = 670V$	$T_{j} = 125^{\circ}C$			650	ns
Qn	Reverse Recovery Charge	$v_{\rm R} = 670 v$ $di_{\rm S}/dt = 100 {\rm A}/{\rm \mu s}$	$T_j = 25^{\circ}C$		3.6		
			$T_j = 125^{\circ}C$		9.72		μC

• dv/dt numbers reflect the limitations of the circuit rather than the device itself. V = 224 didt  $< 700 A (v_T - V - V) = T < 150\%$ 

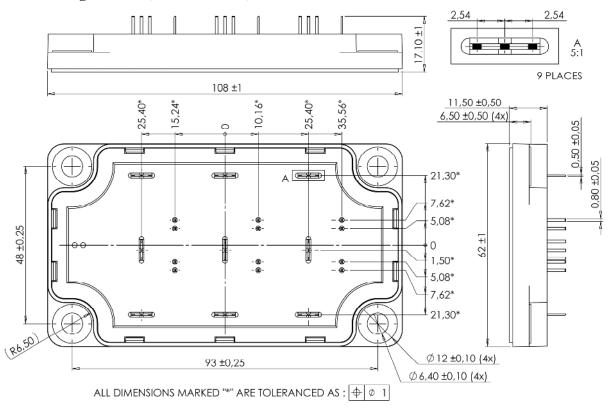
 $I_S \leq \text{-} \ 22A \qquad di/dt \leq 700 A/\mu s \qquad V_R \leq V_{\rm DSS} \qquad T_j \leq 150^\circ C$ 



### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.32	°C/W
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		150	
T <sub>STG</sub>	Storage Temperature Range			-40		125	°C
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

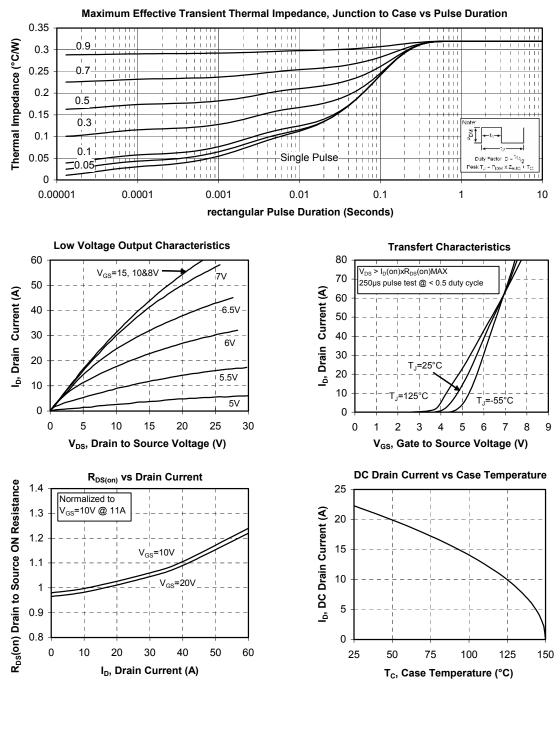
SP6-P Package outline (dimensions in mm)



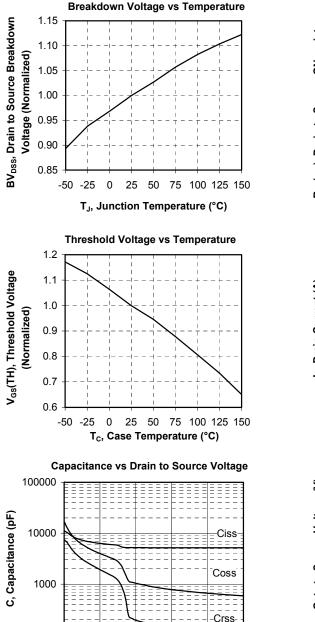
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com



### **Typical Performance Curve**







100

0

10

20

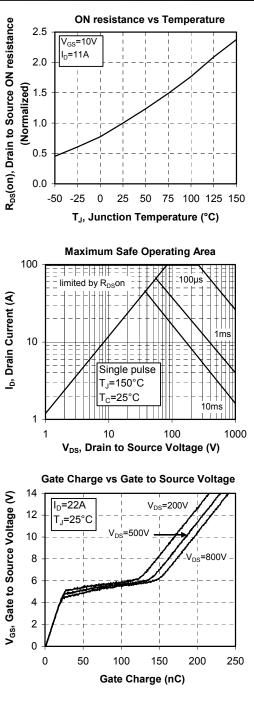
V<sub>DS</sub>, Drain to Source Voltage (V)

30

50

40

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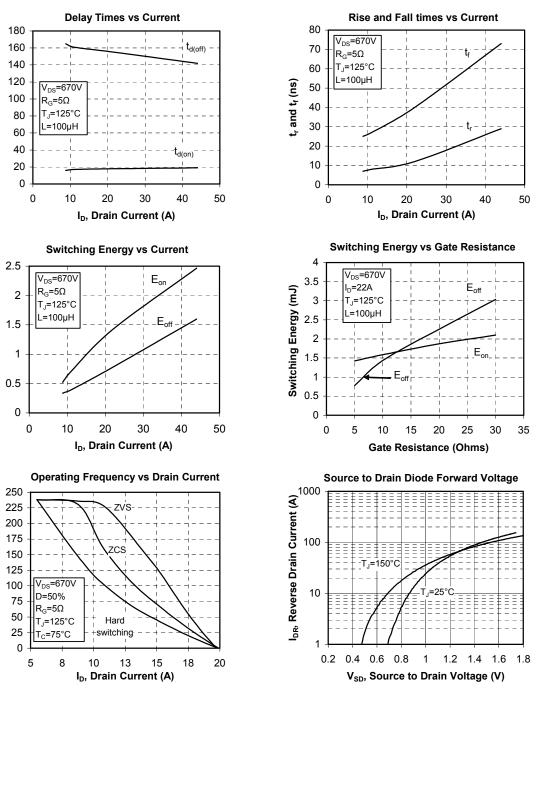


t<sub>d(on)</sub> and t<sub>d(off)</sub> (ns)

Switching Energy (mJ)

Frequency (kHz)

## APTM100TA35FPG



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